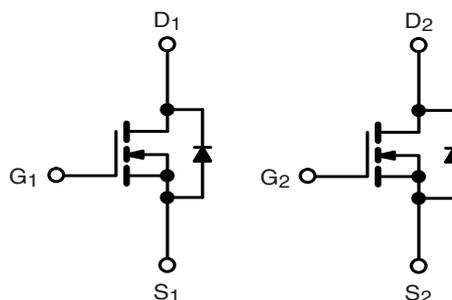


### General Description

The AO4826 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications.

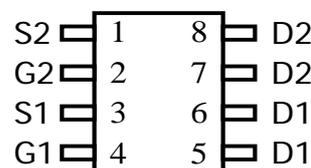


### General Features

$V_{DS} = 60V$   $I_D = 6.3 A$

$R_{DS(ON)} < 25m\Omega$  @  $V_{GS}=10V$

$R_{DS(ON)} < 30m\Omega$  @  $V_{GS}=4.5V$



### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	$T_C = 25\text{ }^\circ\text{C}$	7
		$T_C = 125\text{ }^\circ\text{C}$	4
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	3.6	A
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	28	
Single Pulse Avalanche Current	$I_{AS}$	18	
Single Pulse Avalanche Energy	$E_{AS}$	16.2	mJ
Maximum Power Dissipation <sup>b</sup>	$P_D$	$T_C = 25\text{ }^\circ\text{C}$	4
		$T_C = 125\text{ }^\circ\text{C}$	1.3
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	$R_{thJA}$	110	$^\circ\text{C}/\text{W}$
Junction-to-Foot (Drain)	$R_{thJF}$	34	

#### Notes

- Package limited.
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- When mounted on 1" square PCB (FR4 material).

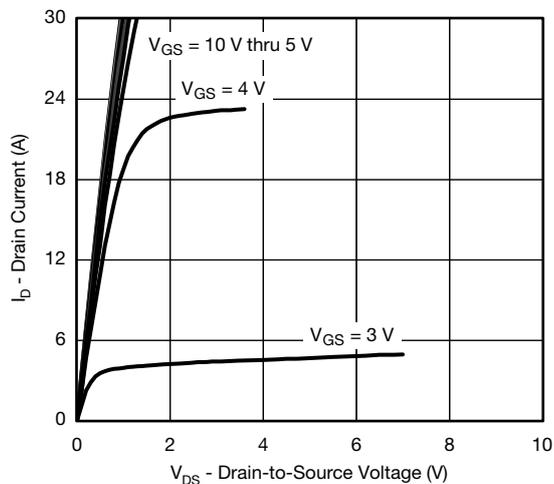
**SPECIFICATIONS** (T<sub>C</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		1	1.5	2.5	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> ≥ 5 V	20	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 4.5 A		20	25	mΩ
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 4 A		22	30	
Forward Transconductance <sup>f</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.5 A		-	15	-	S
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 25 V, f = 1 MHz	-	600	750	pF
Output Capacitance	C <sub>oss</sub>			-	110	140	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	50	62	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	V <sub>DS</sub> = 30 V, I <sub>D</sub> = 5.3 A	-	11.7	18	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			-	1.8	2.7	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	2.8	4.2	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.3	-	6	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 6.8 Ω I <sub>D</sub> ≅ 4.4 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		-	7	11	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			-	3.3	5	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	22.4	33.5	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	2.1	3.2	
Pulsed Current <sup>a</sup>	I <sub>SM</sub> <sup>b</sup>			-	-	28	A
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 2 A, V <sub>GS</sub> = 0 V		-	0.75	1.1	V

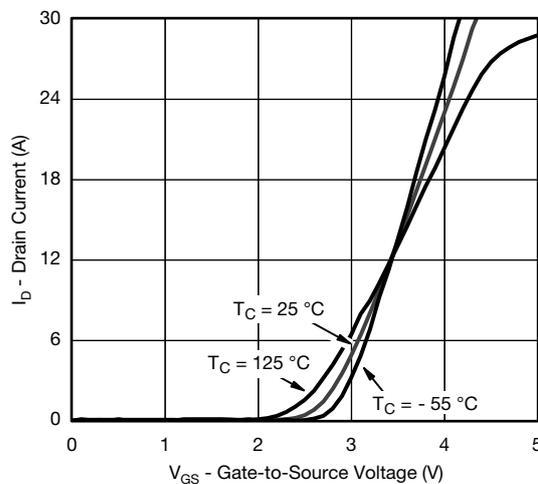
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

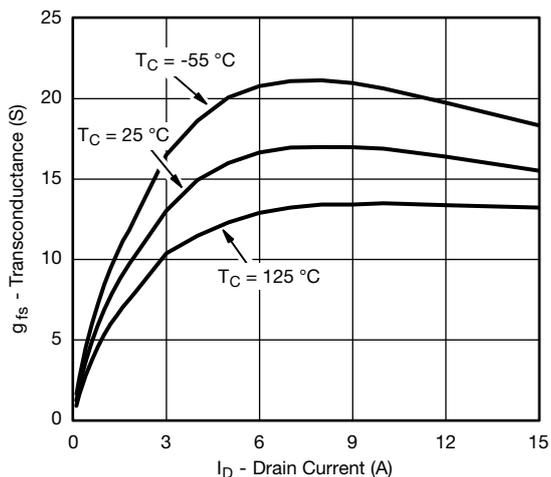
### TYPICAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



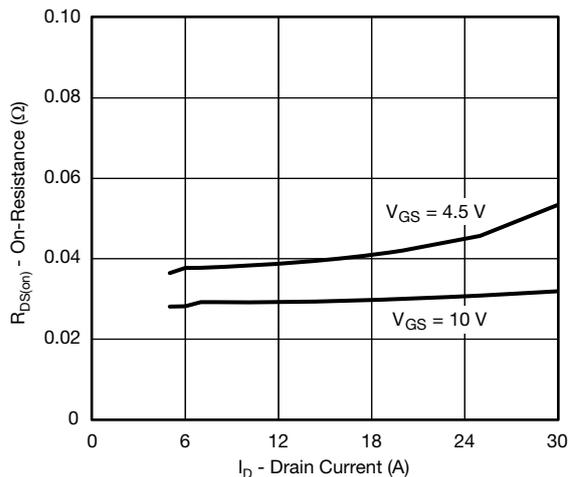
**Output Characteristics**



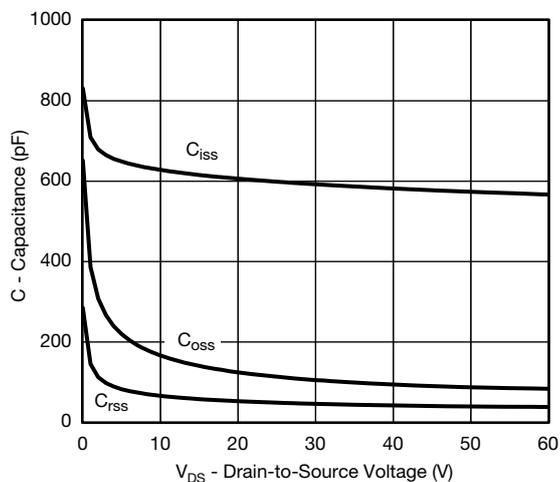
**Transfer Characteristics**



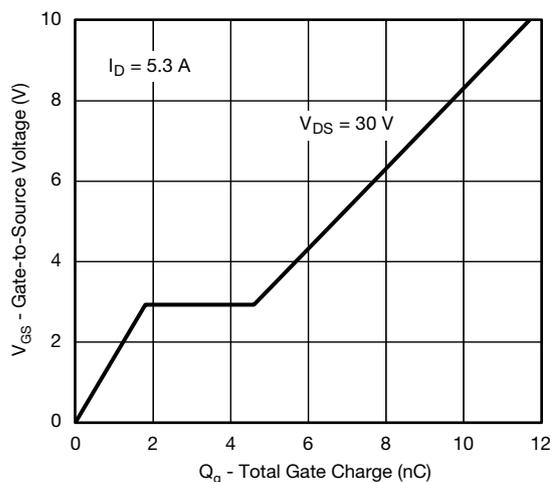
**Transconductance**



**On-Resistance vs. Drain Current**

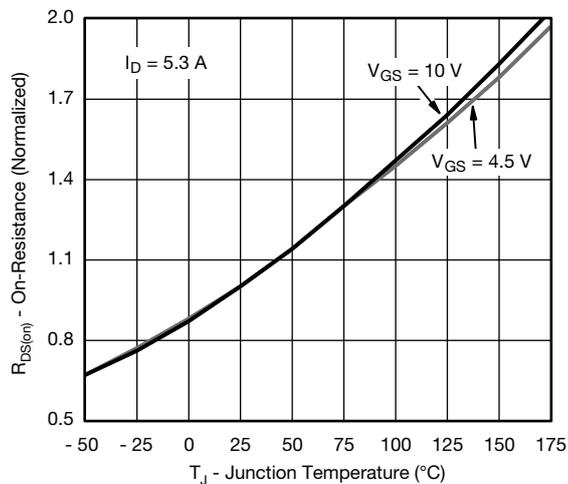


**Capacitance**

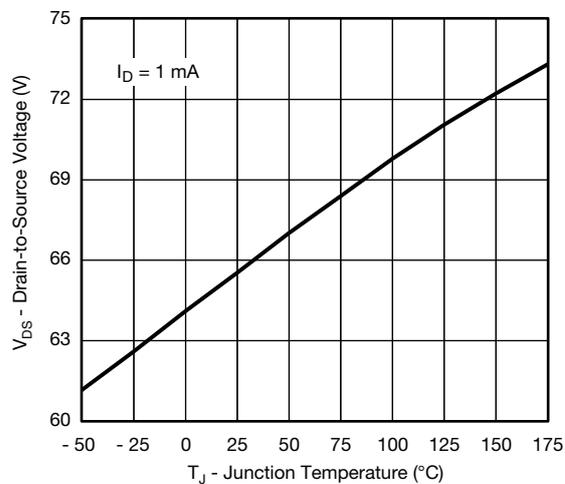


**Gate Charge**

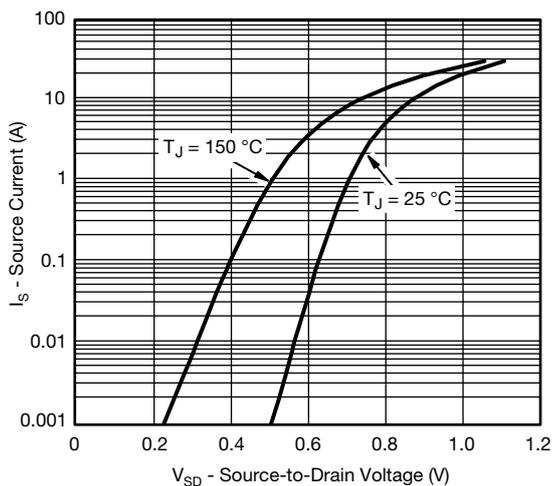
### TYPICAL CHARACTERISTICS ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



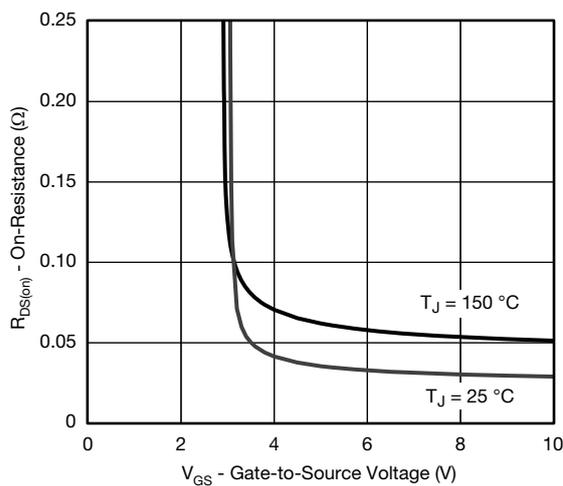
**On-Resistance vs. Junction Temperature**



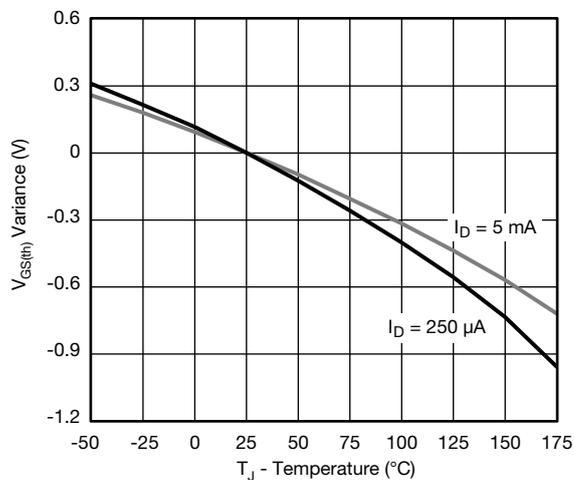
**Drain Source Breakdown vs. Junction Temperature**



**Source Drain Diode Forward Voltage**

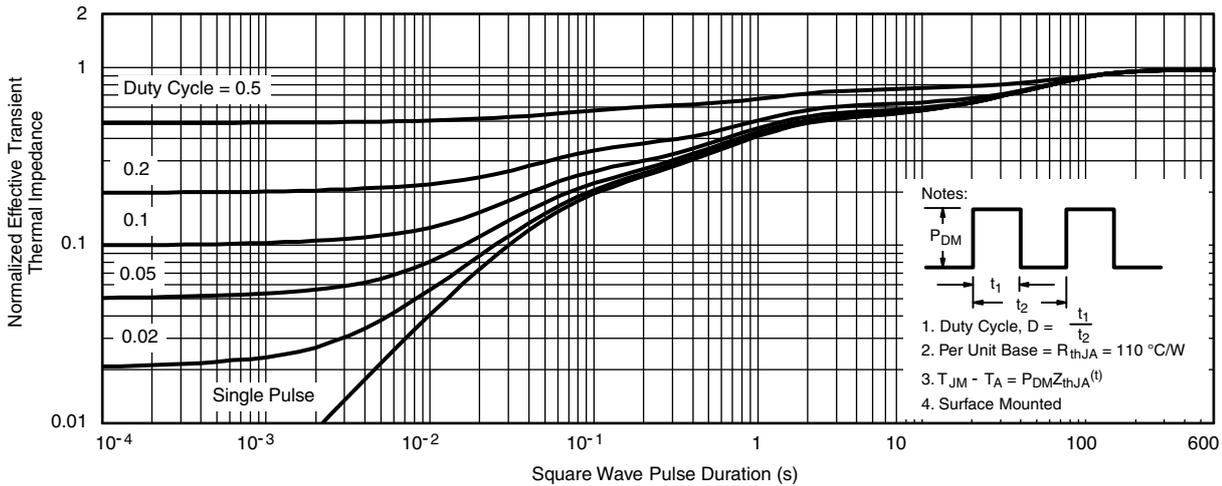
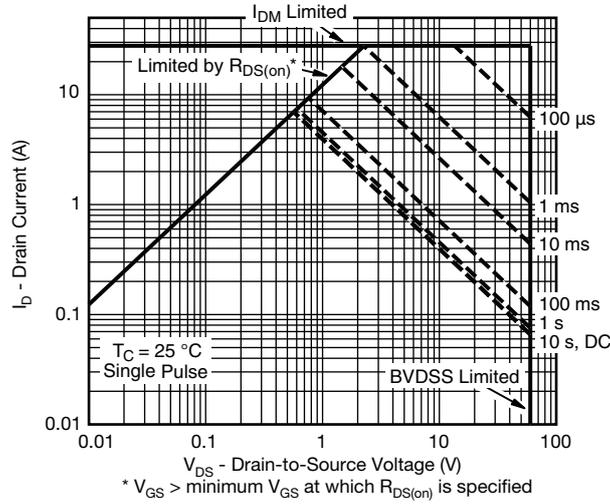


**On-Resistance vs. Gate-to-Source Voltage**



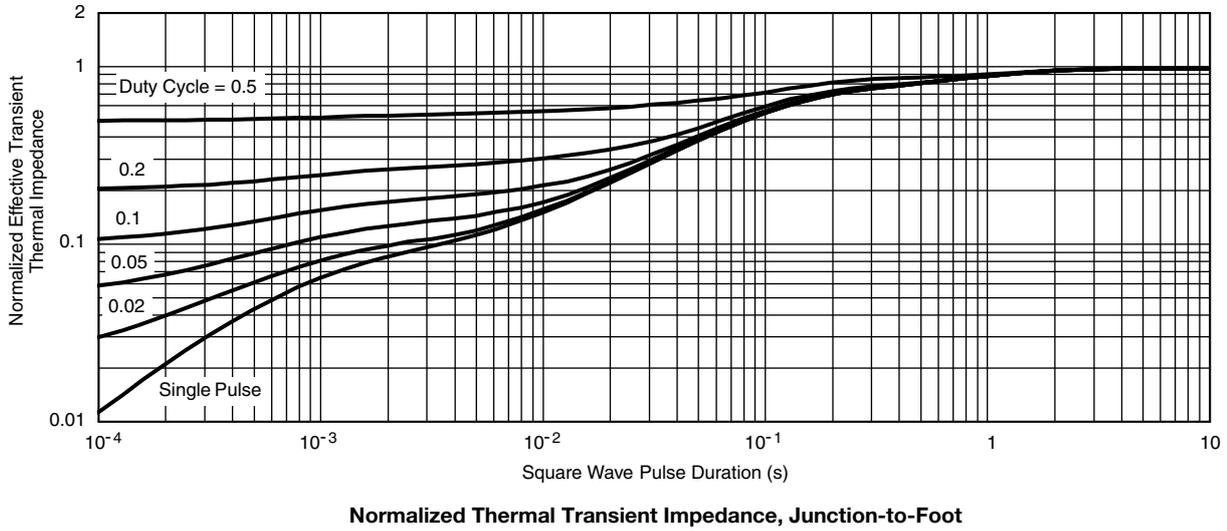
**Threshold Voltage**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



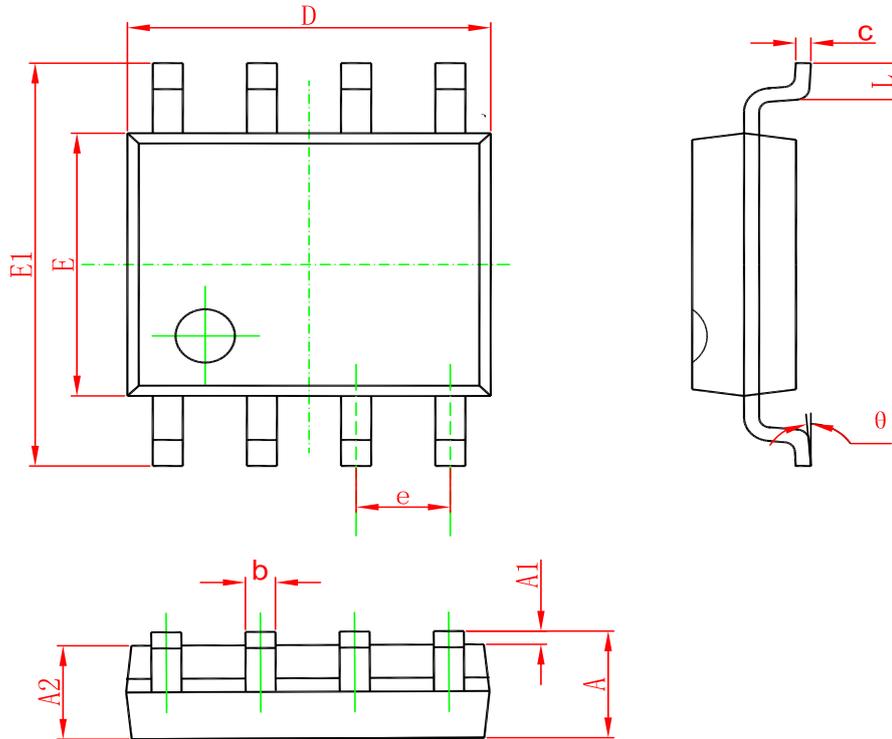
**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



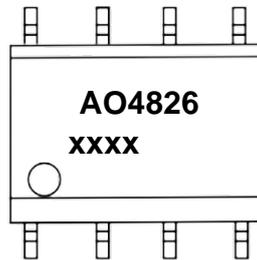
## PACKAGE OUTLINE DIMENSIONS

## SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	<del>1.350</del>	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	<del>4.700</del>	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

## Marking



("xxxx"代表年份周期)

## Ordering information

Order code	Package	Baseqty	Deliverymode
AO4826	SOP-8	3000	Tape and reel